Integrated Relay, Inductive Load Driver

This device is used to switch inductive loads such as relays, solenoids incandescent lamps, and small DC motors without the need of a free-wheeling diode. The device integrates all necessary items such as the MOSFET switch, ESD protection, and Zener clamps. It accepts logic level inputs thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides a Robust Driver Interface Between D.C. Relay Coil and Sensitive Logic Circuits
- Optimized to Switch Relays of 12 V Rail
- Capable of Driving Relay Coils Rated up to 6.0 W at 12 V
- Internal Zener Eliminates the Need of Free-Wheeling Diode
- Internal Zener Clamp Routes Induced Current to Ground for Quieter Systems Operation
- Low V_{DS(ON)} Reduces System Current Drain
- These are Pb-Free Devices

Typical Applications

- Telecom: Line Cards, Modems, Answering Machines, FAX
- Computers and Office: Photocopiers, Printers, Desktop Computers
- Consumer: TVs and VCRs, Stereo Receivers, CD Players, Cassette Recorders
- Industrial: Small Appliances, Security Systems, Automated Test Equipment, Garage Door Openers



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



SOT-23 CASE 318 STYLE 21



JW5 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



SC-74 CASE 318F STYLE 7



JW5 = Specific Device Code

M = Date Code

= Pb-Free Package

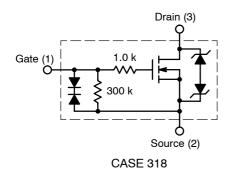
(Note: Microdot may be in either location)

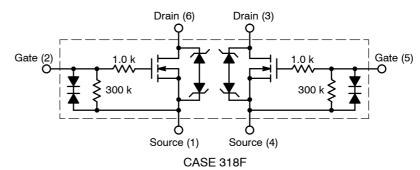
ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3112LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3112DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

INTERNAL CIRCUIT DIAGRAMS





MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise specified)

Symbol	Rating		Value	Unit
V _{DSS}	Drain to Source Voltage – Continuous		14	V_{dc}
V _{GS}	Gate to Source Voltage – Continuous		6	V _{dc}
I _D	Drain Current – Continuous		500	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy (T _{Jinitial} = 25°C)		50	mJ
T_J	Junction Temperature		150	°C
T _A	Operating Ambient Temperature		-40 to 85	°C
T _{stg}	Storage Temperature Range		-65 to +150	°C
P _D	Total Power Dissipation (Note 1) Derating Above 25°C	SOT-23	225 1.8	mW mW/°C
P _D	Total Power Dissipation (Note 1) Derating Above 25°C	SC-74	380 3.0	mW mW/°C
$R_{ hetaJA}$	Thermal Resistance Junction-to-Ambient (Note 1)	SOT-23 SC-74	556 329	°C/W
ESD	Human Body Model (HBM) According to EIA/JESD22/A114		2000	V

^{1.} Mounted onto minimum pad board.

TYPICAL ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit			
OFF CHAR	OFF CHARACTERISTICS							
V _{BRDSS}	Drain to Source Sustaining Voltage (Internally Clamped) (ID = 10 mA)	14	16	17	V			
B _{VGSO}	I _g = 1.0 mA	-	-	8	٧			
I _{DSS}	Drain to Source Leakage Current $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_A = 25^{\circ}\text{C})$ $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_A = 85^{\circ}\text{C})$	- -	- -	20 40	μΑ			
I _{GSS}	Gate Body Leakage Current $(V_{GS} = 3.0 \text{ V}, V_{DS} = 0 \text{ V})$ $(V_{GS} = 5.0 \text{ V}, V_{DS} = 0 \text{ V})$	- -	- -	35 65	μΑ			
ON CHARA	CTERISTICS	•	•					
V _{GS(th)}	Gate Threshold Voltage $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}) $ $ (V_{GS} = V_{DS}, I_D = 1.0 \text{ mA}, T_A = 85^{\circ}\text{C}) $	0.8 0.8	1.2 -	1.4 1.4	V			
R _{DS(on)}	$\begin{array}{l} \text{Drain to Source On-Resistance} \\ (I_D = 250 \text{ mA}, \text{ V}_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 3.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 5.0 \text{ V}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 5.0 \text{ V}, \text{ T}_A = 85^{\circ}\text{C}) \\ (I_D = 500 \text{ mA}, \text{ V}_{GS} = 5.0 \text{ V}, \text{ T}_A = 85^{\circ}\text{C}) \end{array}$	- - - -	- - - -	1.2 1.3 0.9 1.3 0.9	Ω			
I _{DS(on)}	Output Continuous Current $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V})$ $(V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_{A} = 85^{\circ}\text{C})$		400 -	-	mA			
9FS	Forward Transconductance (V _{OUT} = 12.0 V, I _{OUT} = 0.25 A)		490	-	mmhos			

TYPICAL ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Characteristic	Min	Тур	Max	Unit		
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance (V _{DS} = 12 V, V _{GS} = 0 V, f = 10 kHz)	-	23	_	pF		
C _{oss}	Output Capacitance (V _{DS} = 12 V, V _{GS} = 0 V, f = 10 kHz)	_	30	-	pF		
C _{rss}	Transfer Capacitance $(V_{DS} = 12.0 \text{ V}, V_{GS} = 0 \text{ V}, f = 10 \text{ kHz})$	-	7	_	pF		

SWITCHING CHARACTERISTICS

Symbol	Characteristic	Min	Тур	Max	Units
t _{PHL}	Propagation Delay Times: High to Low Propagation Delay; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V) Low to High Propagation Delay; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V)	- -	21 91	- -	nS
t _f t _r	Transition Times: Fall Time; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V) Rise Time; Figure 1 (V_{DS} = 12 V, V_{GS} = 5.0 V)	- -	36 61	- -	nS

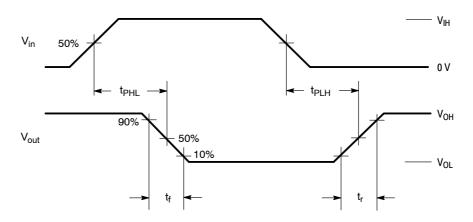


Figure 1. Switching Waveforms

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise specified)

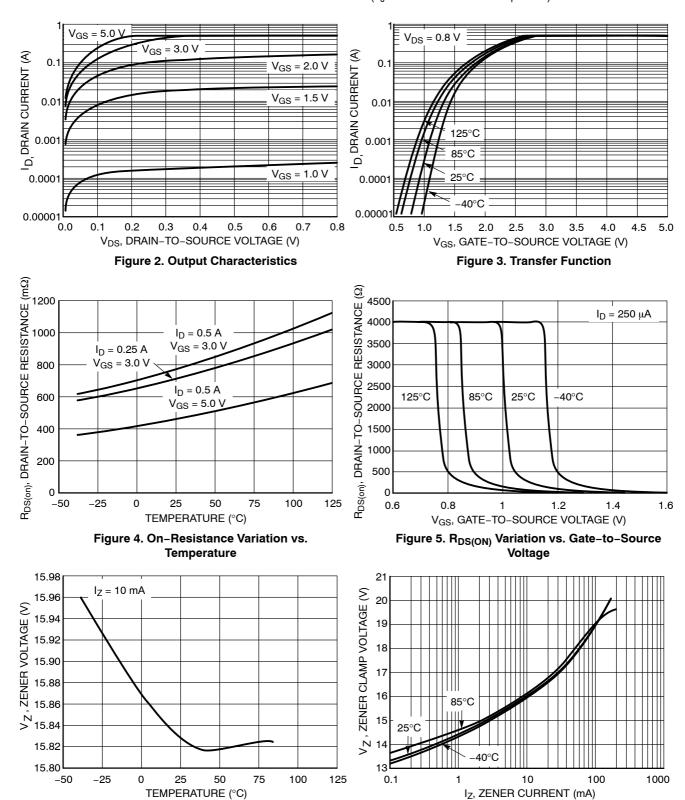
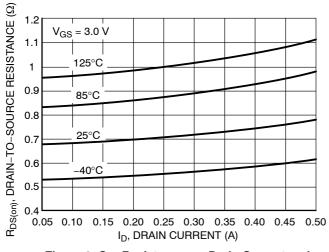


Figure 6. Zener Voltage vs. Temperature

Figure 7. Zener Clamp Voltage vs. Zener Current

$\textbf{TYPICAL PERFORMANCE CURVES} \ (T_J = 25^{\circ}C \ unless \ otherwise \ specified)$



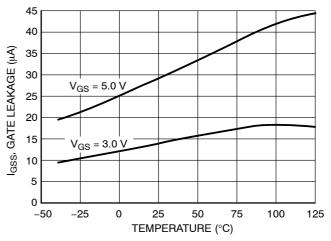


Figure 8. On-Resistance vs. Drain Current and Temperature

Figure 9. Gate Leakage vs. Temperature

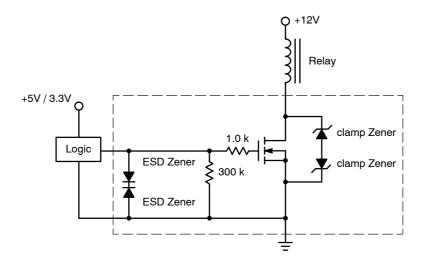
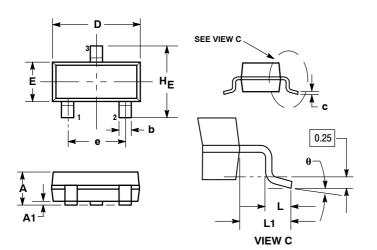


Figure 10. Typical Application Circuit

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**

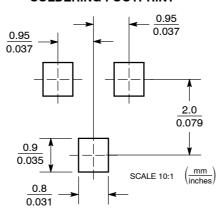


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN

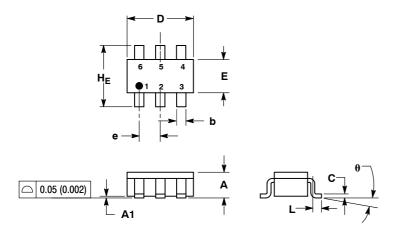
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SC-74 CASE 318F-05 ISSUE M



NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES
 LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 318F-01, -02, -03, -04 OBSOLETE. NEW
- STANDARD 318F-05

	М	ILLIMETE	ETERS INCHES				
DIM	MIN	NOM	MAX	MIN NOM MAX			
Α	0.90	1.00	1.10	0.035	0.039	0.043	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.25	0.37	0.50	0.010	0.015	0.020	
С	0.10	0.18	0.26	0.004	0.004 0.007		
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.30	1.50	1.70	0.051	0.059	0.067	
е	0.85	0.95	1.05	0.034	0.037	0.041	
L	0.20	0.40	0.60	0.008 0.016 0.0		0.024	
HE	2.50	2.75	3.00	0.099	0.108	0.118	
θ	0°	_	10°	0°	-	10°	

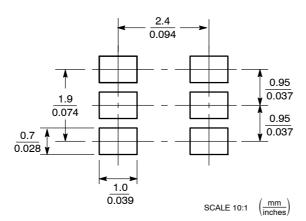
STYLE 7:

- PIN 1. SOURCE 1 2. GATE 1
 - 3.

DRAIN 2 SOURCE 2 GATE 2

6. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and war engineer trademarks of semiconductor components industries, Ite (SciLLC) solitate services are injective to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative